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(54) SEMICONDUCTOR DEVICE  
AND ITS MANUFACTURING  
METHOD

(57) Abstract:

**PROBLEM TO BE SOLVED:** To provide a construction of an MIM capacitor which is suitable for a fine wiring process, has small parasitic resistance and parasitic capacitance and has a high capacitance.

**SOLUTION:** This semiconductor device has a 1st electrode 1 which is formed on a semiconductor substrate and has a flat plane shape as a whole, a dielectric layer 2 which is formed on the 1st electrode and has a flat plane shape as a whole, a 2nd electrode 3 which is formed on the dielectric layer 2 and has a flat plane shape as a whole, an interlayer insulating layer 6 which covers the 1st and 2nd electrodes and the dielectric layer as a whole and has a plurality of via-holes 4 and 7 bottomed by the surface of the 2nd electrode 3 therein, and conductive layers filling the via-holes.

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